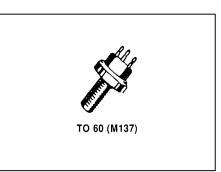


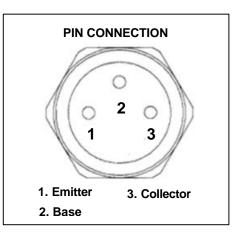
140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013 PHONE: (215) 631-9840 FAX: (215) 631-9855

RF AND MICROWAVE TRANSISTORS VHF – UHF APPLICATIONS

Features

- 130 400 MHz
- 28 Volts
- **High Power Gain**
- **High Efficiency**
- **Common Emitter**
- Pout = 13.5 W Min. @ 175 MHz





°C

°C

+200

-65 to +150

DESCRIPTION:

This silicon epitaxial NPN planar high frequency transistor employs a multi emitter electrode design. This feature together with a heavily diffused base matrix located between the individual emitters results in high RF current handling capability, high power gain, low base resistance and low output capacitance. These transistors are intended for Class A, B, or C amplifier, oscillator or frequency multiplier circuits and are specifically designed for operation in the VHF-UHF region.

| ABSOLUTE MA | AXIMUM RATINGS (Tcase = 25°C) | | |
|------------------|-------------------------------|-------|------|
| Symbol | Parameter | Value | Unit |
| V _{CBO} | Collector-Base Voltage | 65 | V |
| V _{CES} | Collector-Emitter Voltage | 40 | V |
| V_{EBO} | Emitter-Base Voltage | 4.0 | V |
| lc | Device Current | 3.0 | Α |
| PDISS | Power Dissipation | 23.0 | W |

Junction Temperature

Storage Temperature

$\Delta \Box \Delta \Delta$

Thermal Data

T.

TSTG

| R _{TH(j-c)} Junction-Case Thermal Resistance | | | | | | | |
|---|----------|-----|--|--|--|--|--|
| | 7.6 °C/W | 7.6 | | | | | |

Advanced Power Technology reserves the right to change, without notice, the specifications and information contained herein Visit our website at WWW.ADVANCEDPOWER.COM or contact our factory direct.





SD1070

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

| Symbol | Test Conditions | | Value | | |
|-------------------|----------------------------|------|-------|------|-------|
| | | Min. | Тур. | Max. | Units |
| BV _{CBO} | I _c = 0.5 mA | 65 | | | V |
| BVEBO | I _E = 0.25 mA | 4 | | | V |
| BV _{CEO} | I _c = 200 mA | 40 | | | V |
| I _{CEO} | $V_{CE} = 30 V$ | | | 0.25 | mA |
| h _{FE} | $V_{CE} = 5 V$ $I_C = 1 A$ | 5 | | | |

DYNAMIC

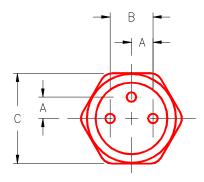
| Symbol | Test Conditions | | | Value | | | |
|----------------|-----------------------------|----------------------|------------------------|-------|------|------|-------|
| Symbol | Symbol Test Conditions | | | Min. | Тур. | Max. | Units |
| Ρουτ | f = 175 MHz P _{II} | _N = 3.5 V | V _{cc} = 28 V | 13.5 | | | W |
| η _c | f = 175 MHz P _{II} | _N = 3.5 V | V _{cc} = 28 V | 70 | | | % |
| G _P | f = 175 MHz P _{II} | _N = 3.5 V | V _{cc} = 28 V | 5.8 | | | dB |
| Сов | f = 1 MHz V _c | _{св} = 30 V | | | | 20 | рF |

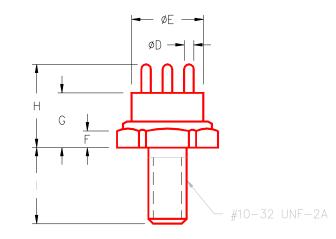


SD1070

PACKAGE MECHANICAL DATA

PACKAGE STYLE M137





| | MINIMUM | махімим | MINIMUM | MAXIMUM |] |
|---|------------|------------|------------|------------|---------------|
| | | | | | |
| | INCHES/MM | INCHES/MM | INCHES/MM | INCHES/MM | |
| A | .090/2,29 | .110/2,79 | .420/10,67 | .455/11,56 | STANDARD STUD |
| В | .185/4,70 | .215/5,46 | .140/3,56 | .160/4,06 | SHORT STUD |
| С | .420/10,67 | .440/11,18 | | | |
| D | .030/0,76 | .046/1,17 | | | |
| E | .320/8,13 | .360/9,14 | | | |
| F | .090/2,29 | .135/3,43 | | | |
| G | .215/5,46 | .320/8,13 | | | |
| Н | | .480/12,19 | | |] |